



IGBT module

SK 15 GH 066

Features*

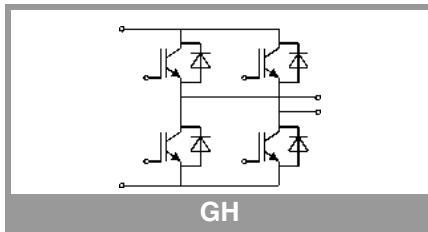
- Compact design
- One screw mounting module
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DBC)
- 600V Trench IGBT3 technology
- 600V CAL IHD diode technology
- Integrated NTC temperature sensor
- UL recognized, file no. E 63 532

Typical Applications

- DC/DC Converter
- Motor Drives
- Welding

Absolute Maximum Ratings		Values	Unit
Symbol	Conditions		
Inverter - IGBT			
V_{CES}	$T_j = 25^\circ\text{C}$	600	V
I_C	$T_j = 175^\circ\text{C}$	24	A
		20	A
I_{Cnom}		15	A
I_{CRM}		30	A
V_{GES}		-20 ... 20	V
t_{psc}	$V_{CC} = 360\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 600\text{ V}$	6	μs
T_j		-40 ... 175	$^\circ\text{C}$
Inverse - Diode			
V_{RRM}	$T_j = 25^\circ\text{C}$	600	V
I_F	$T_j = 175^\circ\text{C}$	32	A
		25	A
I_{IFRM}		30	A
I_{FSM}	10 ms, sin 180°, $T_j = 150^\circ\text{C}$	95	A
T_j		-40 ... 175	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	$\Delta T_{\text{terminal}}$ at PCB joint = 30 K, per pin	60	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC, sinusoidal, $t = 1\text{ min}$	2500	V

Characteristics		min.	typ.	max.	Unit
Symbol	Conditions				
Inverter - IGBT					
$V_{CE(\text{sat})}$	$I_C = 15\text{ A}$ $V_{GE} = 15\text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$	1.45	1.90	V
		$T_j = 150^\circ\text{C}$	1.65	2.05	V
V_{CE0}	chiplevel	$T_j = 25^\circ\text{C}$	0.90	1.00	V
		$T_j = 150^\circ\text{C}$	0.85	0.90	V
r_{CE}	$V_{GE} = 15\text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$	37	60	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	53	77	$\text{m}\Omega$
$V_{GE(\text{th})}$	$V_{GE} = V_{CE}$, $I_C = 0.21\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$, $T_j = 25^\circ\text{C}$			0.1	mA
C_{ies}		$f = 1\text{ MHz}$	0.86		nF
C_{oes}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	0.055		nF
C_{res}		$f = 1\text{ MHz}$	0.024		nF
Q_G	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		100		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		0		Ω
$t_{d(on)}$	$V_{CC} = 300\text{ V}$	$T_j = 150^\circ\text{C}$	9		ns
t_r	$I_C = 15\text{ A}$	$T_j = 150^\circ\text{C}$	9		ns
E_{on}	$R_{G\text{ on}} = 6.2\text{ }\Omega$ $R_{G\text{ off}} = 6.2\text{ }\Omega$	$T_j = 150^\circ\text{C}$	0.3		mJ
$t_{d(off)}$	$di/dt_{\text{on}} = 1506\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	135		ns
t_f	$di/dt_{\text{off}} = 325\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	68		ns
E_{off}	$V_{GE} = +15/-8\text{ V}$	$T_j = 150^\circ\text{C}$	0.35		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{\text{paste}}=0.8\text{ W}/(\text{mK})$		2.19		K/W





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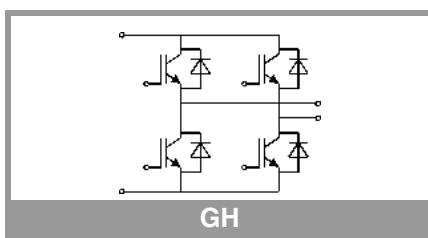
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Characteristics		Symbol	Conditions	min.	typ.	max.	Unit						
Inverse - Diode													
$V_F = V_{EC}$	$I_F = 15 \text{ A}$		$T_j = 25 \text{ }^\circ\text{C}$		1.23	1.48	V						
	chiplevel		$T_j = 150 \text{ }^\circ\text{C}$			1.15	1.34						
V_{FO}	chiplevel		$T_j = 25 \text{ }^\circ\text{C}$		0.99	1.10	V						
			$T_j = 150 \text{ }^\circ\text{C}$			0.80	0.89						
r_F	chiplevel		$T_j = 25 \text{ }^\circ\text{C}$		16	26	$\text{m}\Omega$						
			$T_j = 150 \text{ }^\circ\text{C}$			23	30						
I_{RRM}	$I_F = 15 \text{ A}$		$T_j = 150 \text{ }^\circ\text{C}$		16	A							
	$di/dt_{off} = 1506 \text{ A}/\mu\text{s}$		$T_j = 150 \text{ }^\circ\text{C}$										
Q_{rr}	$V_{GE} = -8 \text{ V}$		$T_j = 150 \text{ }^\circ\text{C}$		1.25	μC							
	$V_{CC} = 300 \text{ V}$		$T_j = 150 \text{ }^\circ\text{C}$										
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=0.8 \text{ W}/(\text{mK})$				0.26		mJ						
					2.7		K/W						
Module													
L_{CE}					-		nH						
M_s	to heatsink			1.8	2		Nm						
W					19		g						



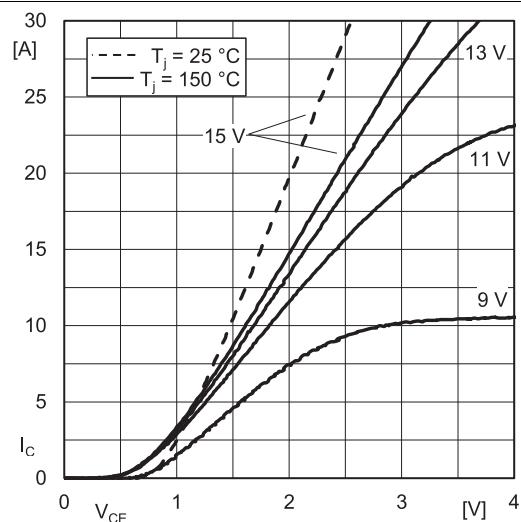
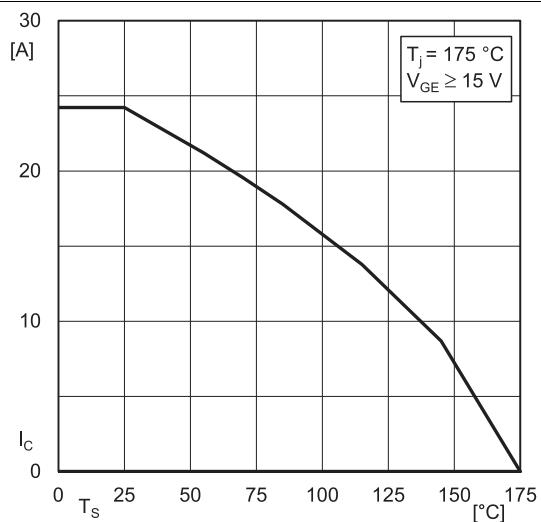
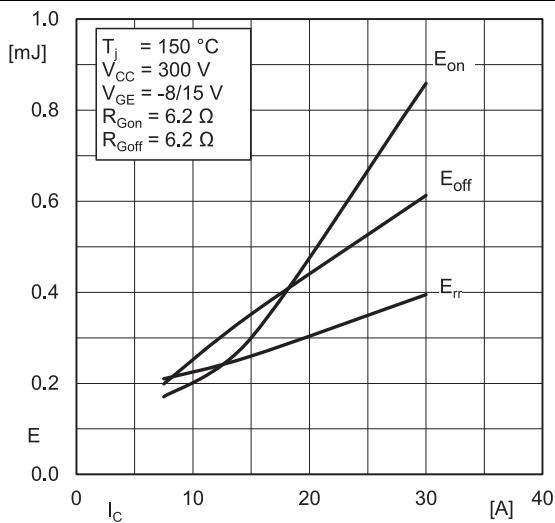
Fig. 1: Typ. IGBT output characteristic, incl. $R_{CC+EE'}$ Fig. 2: Rated current vs. temperature $I_C = f (T_s)$ 

Fig. 3: Typ. turn-on /-off energy = f (I_C)

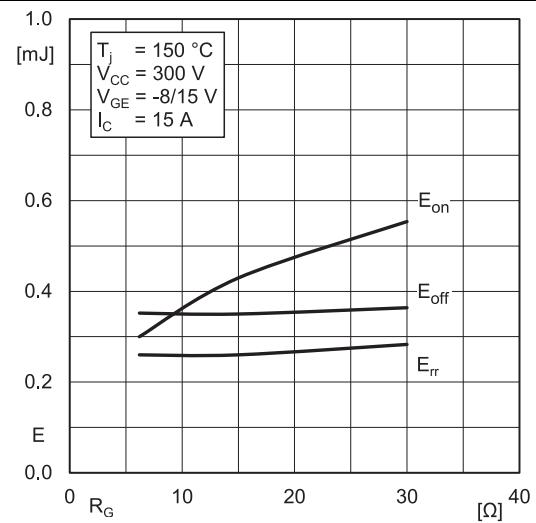


Fig. 4: Typ. turn-on /-off energy = f (R_G)

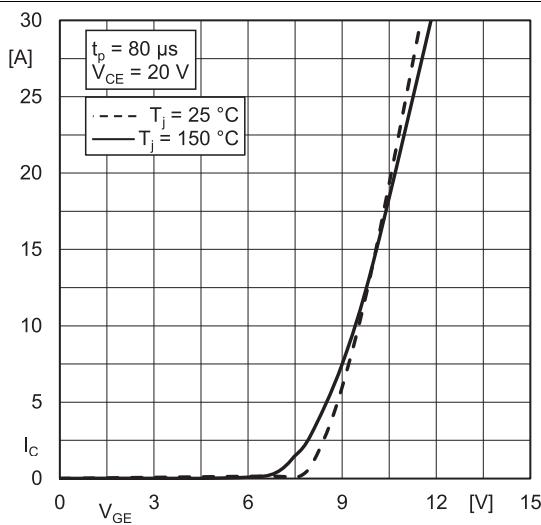


Fig. 5: Typ. IGBT transfer characteristic

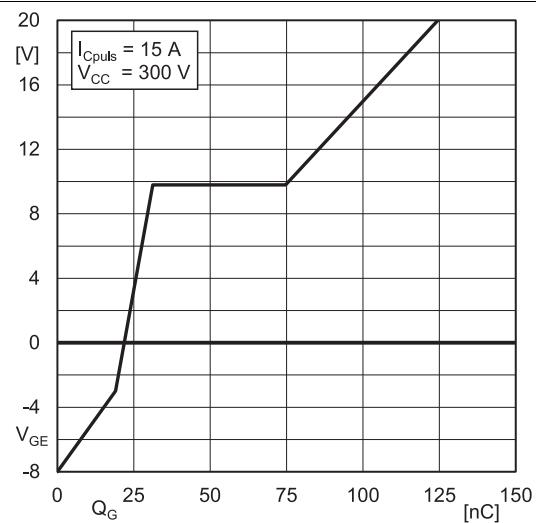


Fig. 6: Typ. IGBT gate charge characteristic

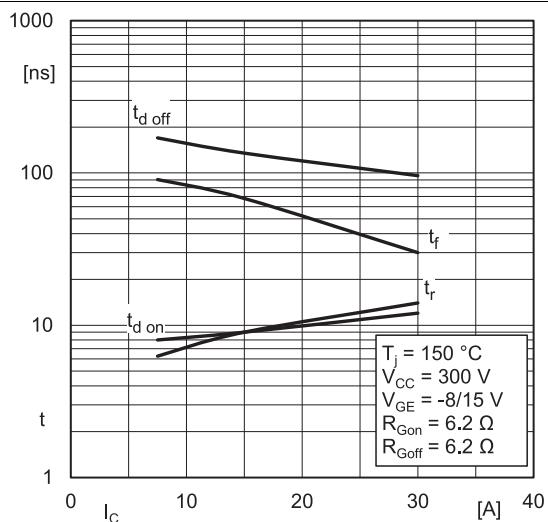


Fig. 7: Typ. switching times = f (I_C)

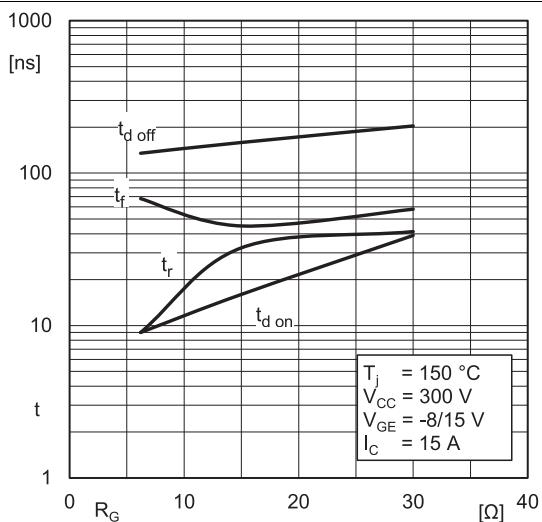


Fig. 8: Typ. switching times = f (R_G)

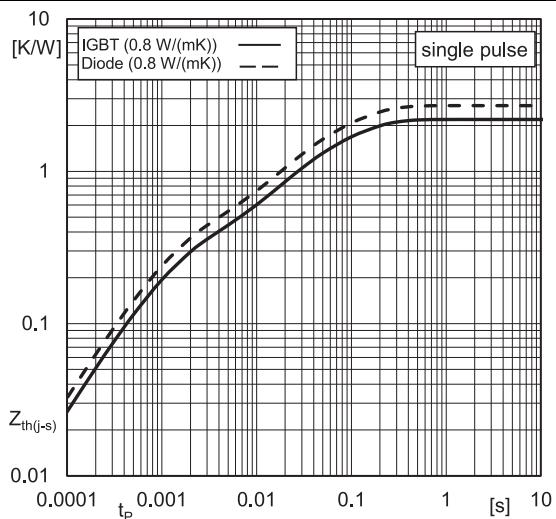


Fig. 9: Typ. transient thermal impedance

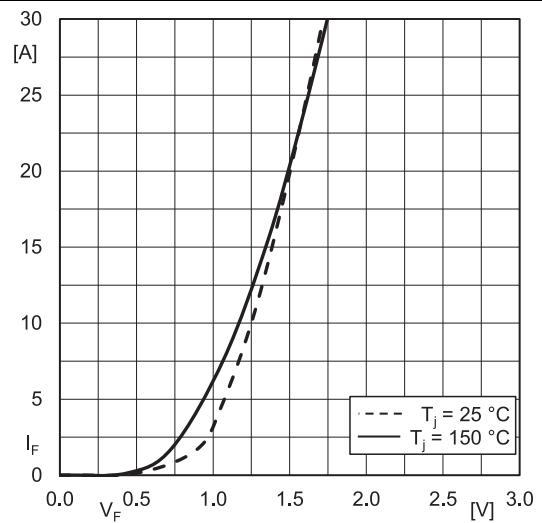


Fig. 10: Typ. Diode forward charact., incl. R_{CC' + EE'}

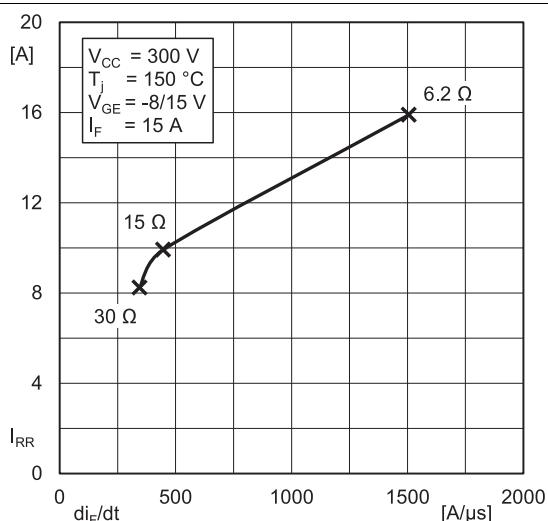


Fig. 11: Typ. Diode peak reverse recovery current

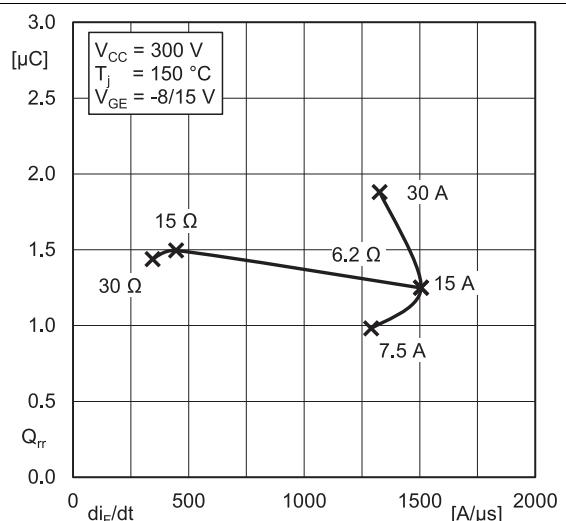
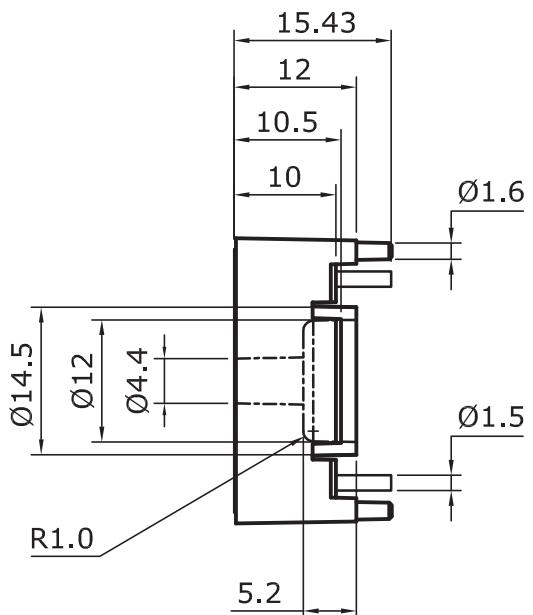
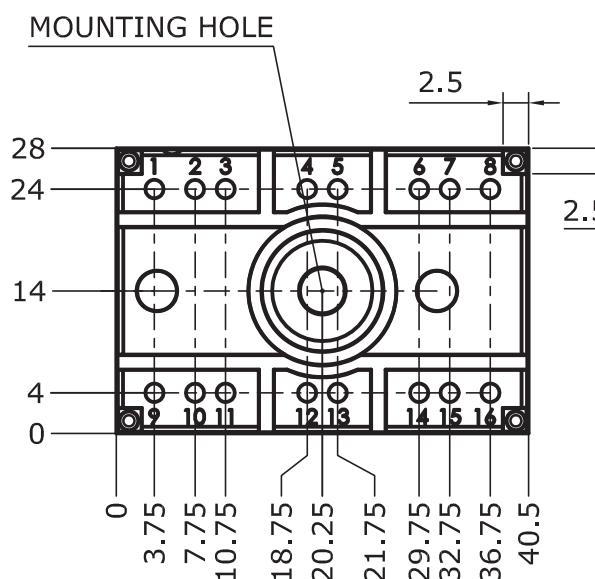
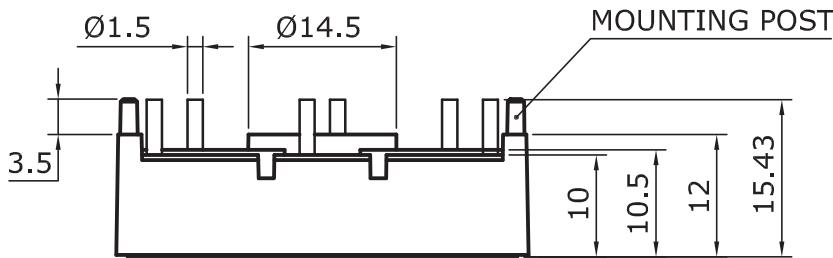


Fig. 12: Typ. Diode reverse recovery charge

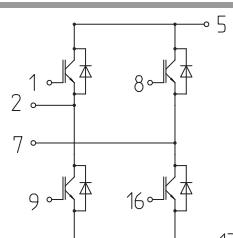
Dimensions: mm
Tolerance system: ISO 2768-m



Suggested hole diameter for solder pins in the circuit board:

- 2.0 mm

SEMITOP®2



GH

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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